Amendments to the Specification

Please replace the paragraph that begins in line 10 on page 16 with the following amended paragraph:

A second embodiment is illustrated in ~~FIGS. 7-12~~ FIGS. 7-8. Referring to FIG. 7, a partially formed transistor that includes a substrate **10** with isolation regions **11**, a gate dielectric layer **12**, a gate layer **13**, and an underlayer **14** is formed as described previously. A top photoresist layer **20** is coated to a thickness of about 500 to 5000 Angstroms. The photoresist layer **20** and underlayer **14** form a bilayer stack. The photoresist layer **20** is preferably a positive tone non-silicon containing photoresist which highly absorbs 157 nm or 193 nm radiation so that during a typical patternwise exposure, only a small portion of the photoresist layer near the surface of an exposed region undergoes a photoinduced reaction. It is understood that a post-exposure bake may be necessary to increase the rate of the photoinduced reaction in order to decrease process time. Alternatively, a shorter wavelength than 157 nm may be used such as a 13 nm wavelength from an EUV source to patternwise expose the photoresist layer **20**. A wavelength of less than 200 nm is preferred to enable the photoresist layer **20** to be selectively exposed in surface regions **21** having a width w_1 of below 100 nm. In an alternative embodiment, a longer exposure wavelength than 200 nm may be used if a width w_1 of about 130 nm or larger is desired.